

CXDM1002N

**SURFACE MOUNT SILICON
N-CHANNEL
ENHANCEMENT-MODE
MOSFET**


www.centralsemi.com
**SOT-89 CASE****APPLICATIONS:**

- Load/Power switches
- Power supply converter circuits
- Battery powered portable equipment

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

	SYMBOL		UNITS
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	20	V
Continuous Drain Current (Steady State)	I_D	2.0	A
Maximum Pulsed Drain Current, $t_p=10\mu\text{s}$	I_{DM}	7.0	A
Power Dissipation	P_D	1.2	W
Operating and Storage Junction Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$
Thermal Resistance	Θ_{JA}	104	$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

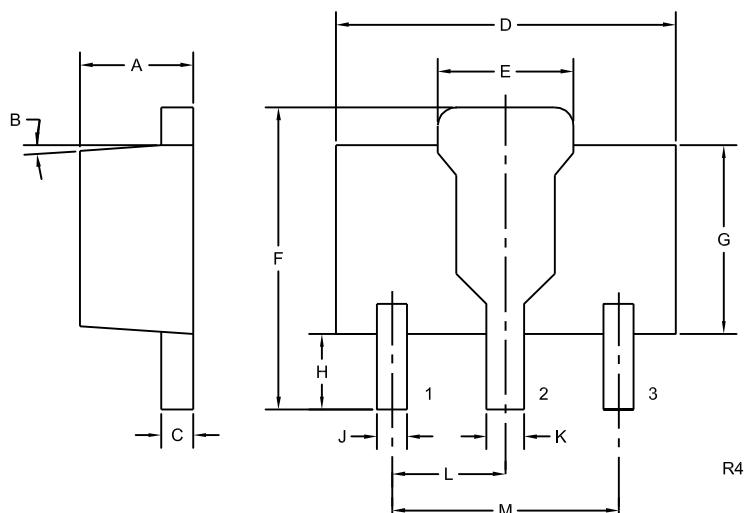
SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{GSSF}, I_{GSSR}	$V_{GS}=20\text{V}, V_{DS}=0$			100	nA
I_{DSS}	$V_{DS}=100\text{V}, V_{GS}=0$			100	nA
BV_{DSS}	$V_{GS}=0, I_D=250\mu\text{A}$	100			V
$V_{GS(\text{th})}$	$V_{GS}=V_{DS}, I_D=250\mu\text{A}$	1.5	2.1	2.5	V
V_{SD}	$V_{GS}=0, I_S=1.0\text{A}$			1.1	V
$r_{DS(\text{ON})}$	$V_{GS}=10\text{V}, I_D=2.0\text{A}$	125		300	$\text{m}\Omega$
$r_{DS(\text{ON})}$	$V_{GS}=4.5\text{V}, I_D=1.0\text{A}$	140		350	$\text{m}\Omega$
C_{rss}	$V_{DS}=25\text{V}, V_{GS}=0, f=1.0\text{MHz}$	48			pF
C_{iss}	$V_{DS}=25\text{V}, V_{GS}=0, f=1.0\text{MHz}$	550			pF
C_{oss}	$V_{DS}=25\text{V}, V_{GS}=0, f=1.0\text{MHz}$	45			pF
$Q_{g(\text{tot})}$	$V_{DS}=80\text{V}, V_{GS}=5.0\text{V}, I_D=2.0\text{A}$	6.0			nC
Q_{gs}	$V_{DS}=80\text{V}, V_{GS}=5.0\text{V}, I_D=2.0\text{A}$	1.2			nC
Q_{gd}	$V_{DS}=80\text{V}, V_{GS}=5.0\text{V}, I_D=2.0\text{A}$	3.0			nC
t_{on}	$ V_{DD}=50\text{V}, V_{GS}=5.0\text{V}, I_D=3.5\text{A} $	32			ns
t_{off}	$ R_G=4.7\Omega $		50		ns

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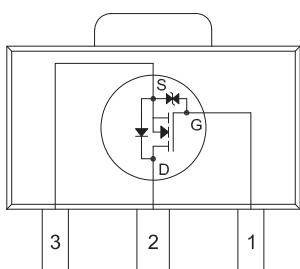
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SOT-89 CASE - MECHANICAL OUTLINE



PIN CONFIGURATION



(Top View)
Tab is common to pin 2

LEAD CODE:

- 1) Gate
- 2) Drain
- 3) Source

MARKING: FULL PART NUMBER

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.055	0.067	1.40	1.70
B	4°		4°	
C	0.014	0.018	0.35	0.46
D	0.173	0.185	4.40	4.70
E	0.064	0.074	1.62	1.87
F	0.146	0.177	3.70	4.50
G	0.090	0.106	2.29	2.70
H	0.028	0.051	0.70	1.30
J	0.014	0.019	0.36	0.48
K	0.017	0.023	0.44	0.58
L	0.059		1.50	
M	0.118		3.00	

SOT-89 (REV: R4)

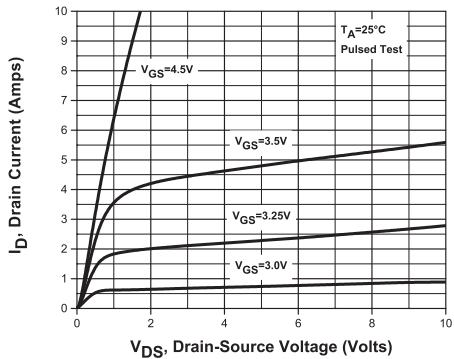
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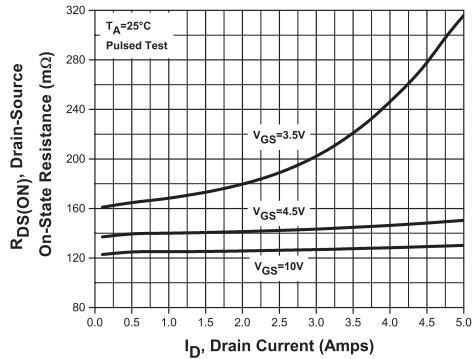


TYPICAL ELECTRICAL CHARACTERISTICS

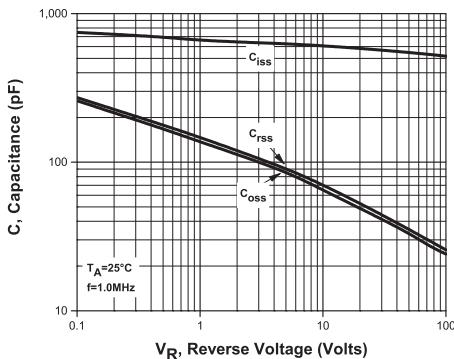
Output Characteristics



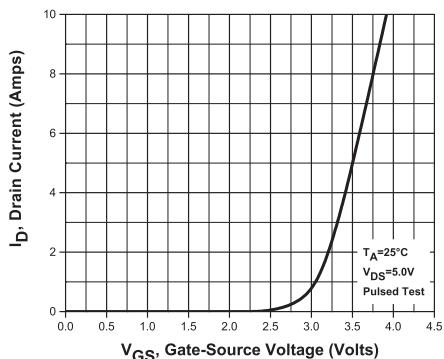
Drain Source On Resistance



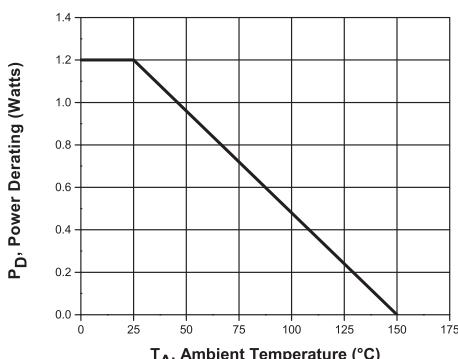
Capacitance



Transfer Characteristics



Power Derating



R1 (19-March 2013)

OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

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